

PSMN022-30PL

N-channel 30 V 22 mΩ logic level MOSFET Rev. 02 — 1 November 2010

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
-				. , P		
V _{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	30	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	-	30	Α
P_{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	41	W
T _j	junction temperature		-55	-	175	°C
Static characteristics						
Doon	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A};$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure } 13}{}$	-	27	34	mΩ
		$V_{GS} = 10 \text{ V; } I_D = 5 \text{ A;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure } 13}{}$	-	19	22	mΩ
Dynamic cl	naracteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A};$	-	1.4	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4.4	-	nC
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 30 A; V_{sup} ≤ 30 V; R_{GS} = 50 Ω ; unclamped	-	-	7	mJ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN022-30PL	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	30	V	
V_{DGR}	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ	-	30	V	
V_{GS}	gate-source voltage		-20	20	V	
I _D	drain current	$V_{GS} = 10 \text{ V; } T_{mb} = 100 \text{ °C; see } \frac{\text{Figure 1}}{}$	-	22	Α	
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	30	Α	
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3	-	125	Α	
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	41	W	
T _{stg}	storage temperature		-55	175	°C	
Tj	junction temperature		-55	175	°C	
Source-drain	diode					
Is	source current	T _{mb} = 25 °C	-	30	Α	
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	125	Α	
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 30 A; V_{sup} ≤ 30 V; R_{GS} = 50 Ω ; unclamped	-	7	mJ	

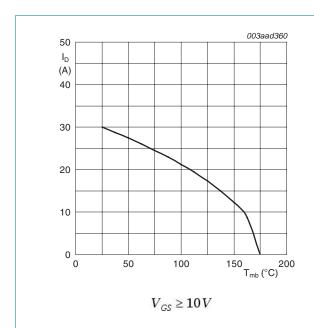
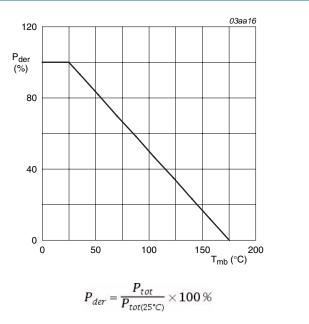


Fig 1. Continuous drain current as a function of mounting base temperature



y 2. Normalized total power dissipation as a function of mounting base temperature

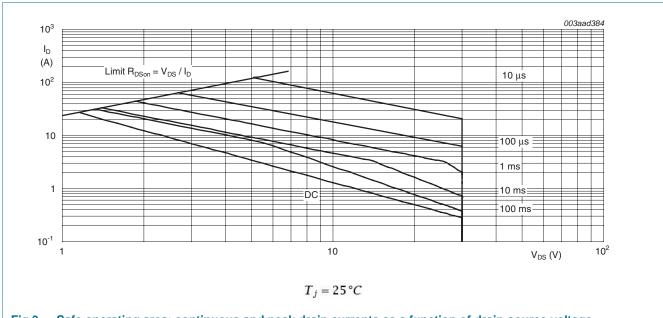


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	3.1	3.6	K/W

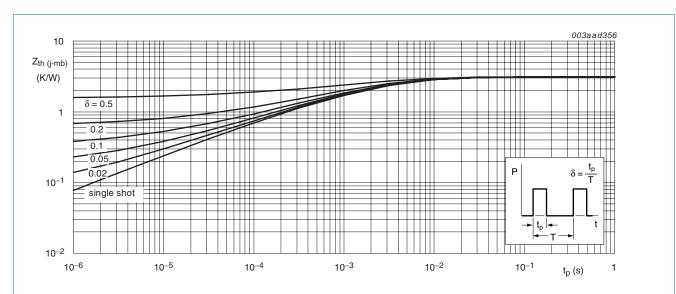


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	11.00
	and the second s			קעי	IVIAX	Unit
Static character	ristics					
(5.1)500	drain-source breakdown	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	30	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	1.3	1.7	2.15	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 11	0.5	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 11	-	-	2.45	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.3	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	50	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
Doon	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 175 °C;$ see <u>Figure 12</u>	-	-	64.6	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 13	-	27	34	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 175 °C;$ see <u>Figure 12</u>	-	35	41.8	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12	-	-	31	mΩ	
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	19	22	mΩ
R_G	gate resistance	f = 1 MHz	-	2	-	Ω
Dynamic charac	cteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 5 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15	-	9	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	8	-	nC
		$I_D = 5 A$; $V_{DS} = 15 V$; $V_{GS} = 4.5 V$;	-	4.4	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	1.6	-	nC
	pre-threshold gate-source charge	$I_D = 5 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 4.5 \text{ V}$; see Figure 14	-	8.0	-	nC
(- 1 /	post-threshold gate-source charge		-	8.0	-	nC
Q_GD	gate-drain charge	$I_D = 5 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 4.5 \text{ V}$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	1.4	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V _{DS} = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	3	-	V
C _{iss}	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	447	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	96	-	pF
	reverse transfer capacitance		-	61	-	pF

 Table 6.
 Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 1.5 \Omega; V_{GS} = 4.5 \text{ V};$ $R_{G(ext)} = 4.7 \Omega$	-	12	-	ns
t _r	rise time		-	29	-	ns
t _{d(off)}	turn-off delay time		-	17	-	ns
t _f	fall time		-	7	-	ns
Source-dra	in diode					
V_{SD}	source-drain voltage	$I_S = 5 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see <u>Figure 17</u>	-	0.7	1.2	V
t _{rr}	reverse recovery time	$I_S = 5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$ $V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}$	-	22	-	ns
Q _r	recovered charge		-	10	-	nC

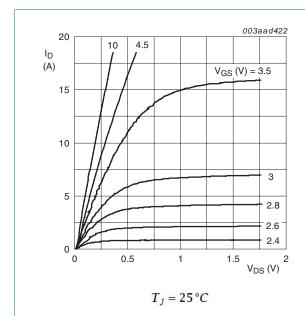


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

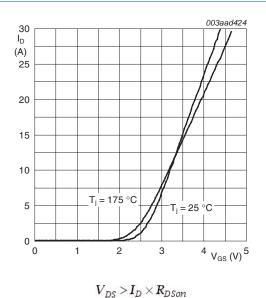


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

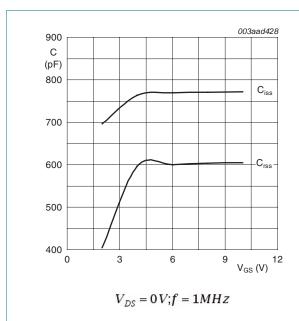


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

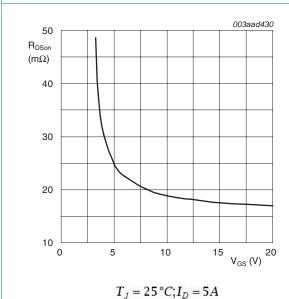


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

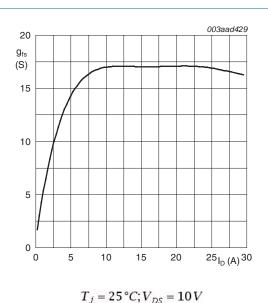
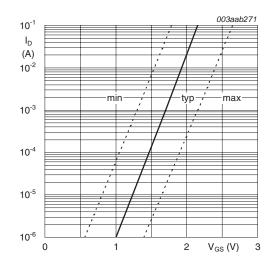
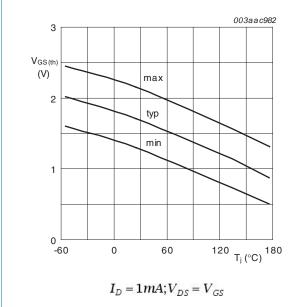


Fig 8. Forward transconductance as a function of drain current; typical values

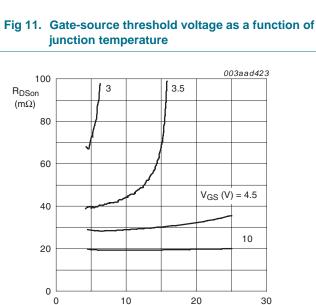


 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



junction temperature



 $I_D(A)$

 $T_j = 25 \,^{\circ}C$

Fig 13. Drain-source on-state resistance as a function

of drain current; typical values

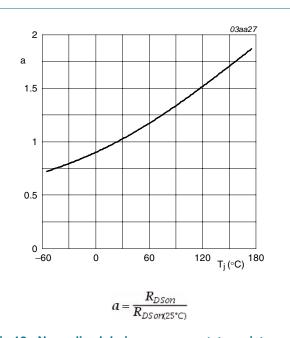


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

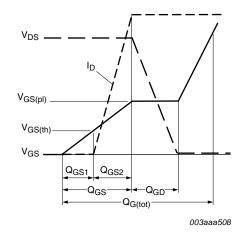


Fig 14. Gate charge waveform definitions

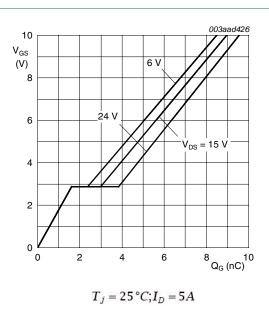
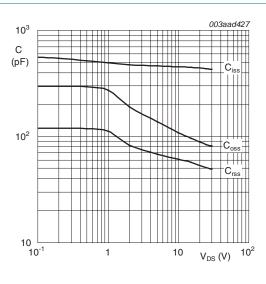
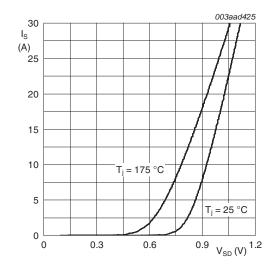


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

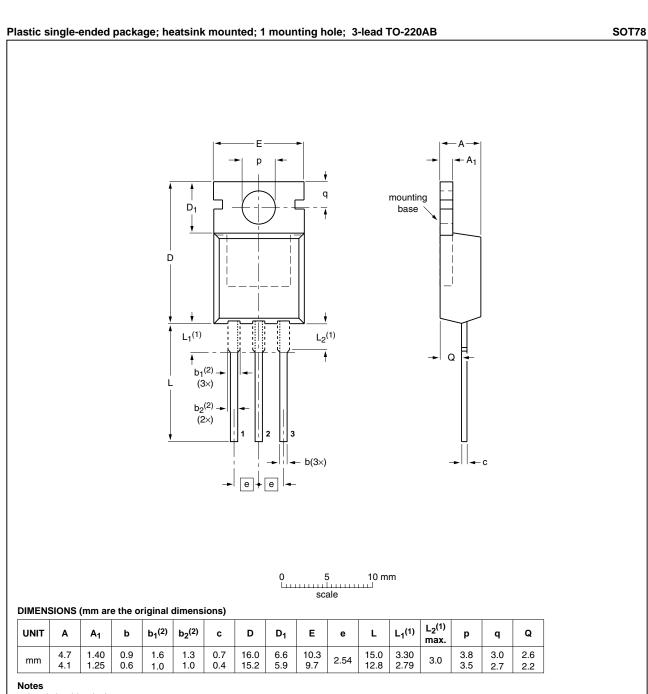
Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $V_{GS} = 0V$

Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline



- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE REF		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13	

Fig 18. Package outline SOT78 (TO-220AB)

PSMN022-30PL

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN022-30PL v.2	20101101	Product data sheet	-	PSMN022-30PL v.1
Modifications:	 Various change 			
PSMN022-30PL v.1	20101018	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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PSMN022-30PL

Nexperia

N-channel 30 V 22 mΩ logic level MOSFET

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